

**Amendments to the Claims:**

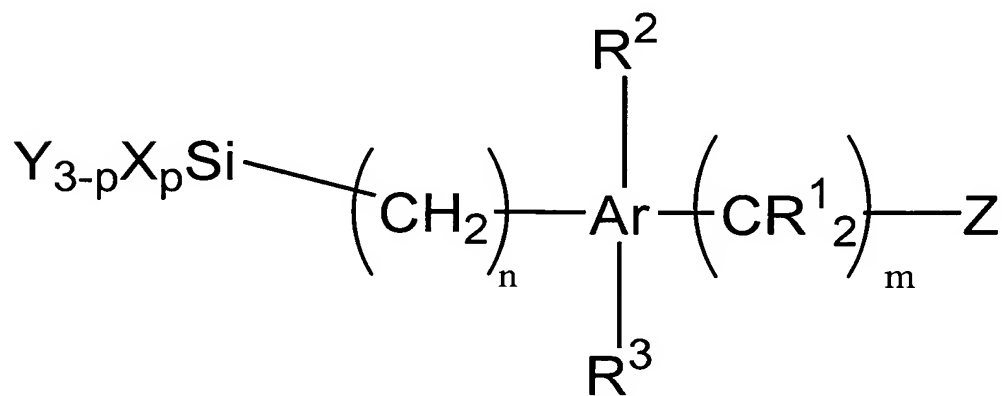
The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for manufacturing a ~~molecular~~-film pattern, comprising:

forming a ~~molecular~~-film by using a ~~photolytic~~an organic silicon compound ~~that contains an aromatic hydrocarbon group~~, as a starting material; and

irradiating the ~~molecular~~-film with a light,

the organic silicon compound having a chemical structure represented by



n, m, p, Ar, X, Y, R<sup>1</sup>, R<sup>2</sup> and R<sup>3</sup> are as follows:

n is an integer of 0 or more;

m is an integer of 0 or more;

p is an integer of 0 or more;

Ar is an aryl group;

R<sup>1</sup> is a hydrogen atom or a fluorine atom;

R<sup>2</sup> is a hydrogen atom, a halogen atom, a perfluoroalkyl group, a hydroxy group, a thiol group, an amino group, an alkylamino group, an alkoxy group, an alkyl group containing a hydroxy group, an alkyl group containing a thiol group, an alkyl group

containing an amino group, an alkyl group containing an alkyl amino group, an organic silicon group, or an alkyl group containing an organic silicon group;

R<sup>3</sup> is a hydrogen atom, a halogen atom, a perfluoroalkyl group, a hydroxy group, a thiol group, an amino group, an alkylamino group, an alkoxy group, an alkyl group containing a hydroxy group, an alkyl group containing a thiol group, an alkyl group containing an amino group, an alkyl group containing an alkyl amino group, an organic silicon group, or an alkyl group containing an organic silicon group;

X is a halogen group including a chlorine group, amino group, or an alkoxy group;

Y is an alkyl group, an aryl group, or hydrogen atom; and

Z is an alkyl group, a perfluoroalkyl group, a silyl group, a cyano group, or a thiol group.

2-23. (Canceled)

24. (New) The method according to claim 1,  
the organic silicon compound having an affinity atom having affinity to  
a silicon atom included in the organic silicon compound, and  
the affinity atom being adjacent spatially to the silicon atom.

25. (New) The method according to claim 24,  
the affinity atom being a halogen atom including a fluorine atom, a nitrogen atom, or  
an oxygen atom.

26. (New) The method according to claim 1,  
the organic silicon compound having at least one of of R<sup>2</sup> and R<sup>3</sup> at an ortho-position  
of the aryl group toward a substituent containing a silyl group of the organic silicon  
compound.

27. (New) A method for manufacturing a film pattern, comprising:

forming a film by using an organic silicon compound that contains an aryl group as starting material,

the organic silicon compound having a first substituent and a second substituent on the aryl group,

the first substituent containing a silicon atom, and

the second substituent being disposed at an ortho-position of the aryl group toward the first substituent.

28. (New) The method according to claim 27,

the second substituent containing an affinity atom having affinity to the silicon atom.

29. (New) The method according to claim 27,

the aryl group being a phenyl group, a biphenyl, a pyridyl group, a naphthyl group, an anthryl group, or a phenanthryl.

30. (New) The method according to claim 28,

the affinity atom being a halogen atom including a fluorine atom, a nitrogen atom, or an oxygen atom.

31. (New) The method according to claim 28,

the organic silicon compound having a bond between the silicon atom and an atom, and

the affinity atom assisting breakage of the bond.

32. (New) The method according to claim 28,

the affinity atom reducing energy of breakage of the bond.

33. (New) The method according to claim 28,

the affinity atom being adjacent spatially to the silicon atom.

34. (New) A method for manufacturing a film pattern, comprising:

forming a film by using an organic silicon compound that contains an aryl group as starting material,

the organic silicon compound having a first substituent and a second substituent on the aryl group,

the first substituent containing a silicon atom,

the second substituent containing an affinity atom having affinity to the silicon atom,

and

the affinity atom being adjacent spatially to the silicon atom.

35. (New) The method according to claim 34,

the affinity atom assisting breakage of a bond between the silicon atom and an atom.

36. (New) The method according to claim 34,

the affinity atom reducing energy of breakage of the bond.

37. (New) The method according to claim 1,

Ar of the chemical structure being a benzene, a naphthalene, biphenyl, pyridine, anthracene, or phenanthrene.

38. (New) The method according to claim 1,

R<sup>1</sup>, and Z of the chemical structure being a fluorine atom and a perfluoroalkyl group, respectively.

39. (New) The method according to claim 1,

the thickness of the film being less than about 3 nm.

40. (New) A method for manufacturing a semiconductor device, comprising:

providing a base member; and

forming a film pattern by the method according to claim 1 above the base member.

41. (New) A method for manufacturing an electro-optical device, comprising:

providing a base member; and

forming a film pattern by the method according to claim 1 above the base member.

42. (New) A method for manufacturing an electronic device comprising:

providing a base member; and

forming a film pattern by the method according to claim 1 above the base member.